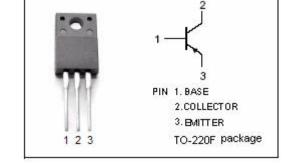


# **isc Silicon PNP Power Transistor**

### **DESCRIPTION**

- · Collector-Emitter Breakdown Voltage-
  - : V<sub>(BR)CEO</sub>= -60V(Min)
- DC Current Gain-
  - :  $h_{FE}$ = 40(Min)@  $I_{C}$ = -1A
- Complement to Type 2SC3851
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

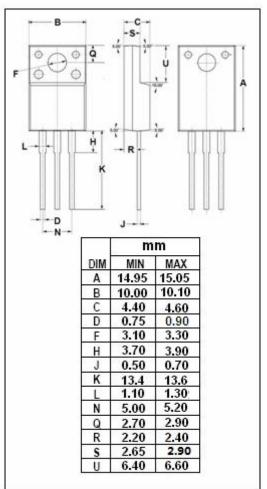


### **APPLICATIONS**

• Designed for audio and general purpose applications.

## ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

| SYMBOL           | PARAMETER                                  | VALUE   | UNIT       |
|------------------|--|---------|------------|
| V <sub>CBO</sub> | Collector-Base Voltage                     | -60     | ٧          |
| Vceo             | Collector-Emitter Voltage                  | -60     | V          |
| V <sub>EBO</sub> | Emitter-Base Voltage                       | -6      | V          |
| lc               | Collector Current-Continuous               | -4      | Α          |
| lΒ               | Base Current-Continuous                    | -1      | Α          |
| Pc               | Collector Power Dissipation<br>@Tc=25°C 25 |         | W          |
| TJ               | Junction Temperature                       | 150     | $^{\circ}$ |
| T <sub>stg</sub> | Storage Temperature                        | -55~150 | $^{\circ}$ |



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### **ISC Silicon PNP Power Transistor**

2SA1488

### **ELECTRICAL CHARACTERISTICS**

Tj=25℃ unless otherwise specified

| SYMBOL               | PARAMETER                            | CONDITIONS  | MIN | TYP. | MAX  | UNIT       |
|----------------------|--------------------------------------|---|-----|------|------|------------|
| V <sub>(BR)CEO</sub> | Collector-Emitter Breakdown Voltage  | I <sub>C</sub> = -25mA; I <sub>B</sub> = 0          | -60 |      |      | V          |
| V <sub>CE(sat)</sub> | Collector-Emitter Saturation Voltage | I <sub>C</sub> = -2A; I <sub>B</sub> = -0.2A        |     |      | -0.5 | V          |
| I <sub>CBO</sub>     | Collector Cutoff Current             | V <sub>CB</sub> = -60V; I <sub>E</sub> = 0          |     |      | -100 | μ <b>A</b> |
| I <sub>EBO</sub>     | Emitter Cutoff Current               | V <sub>EB</sub> = -6V; I <sub>C</sub> = 0           |     |      | -100 | μ <b>A</b> |
| h <sub>FE</sub>      | DC Current Gain                      | I <sub>C</sub> = -1A; V <sub>CE</sub> = -4V         | 40  |      |      |            |
| Сов                  | Output Capacitance                   | I <sub>E</sub> = 0; V <sub>CB</sub> = -10V; f= 1MHz |     | 90   |      | pF         |



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